

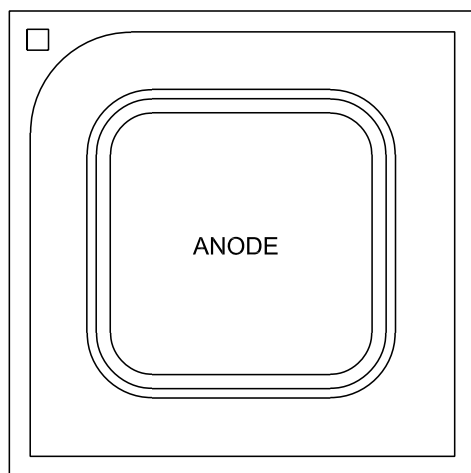
PROCESS CPD98V
Schottky Diode
Silicon High Current Schottky Diode Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

| | |
|------------------------|------------------|
| Process | EPITAXIAL PLANAR |
| Die Size | 11 x 11 MILS |
| Die Thickness | 7.1 MILS |
| Anode Bonding pad Area | 6.3 x 6.3 MILS |
| Top Side Metalization | Al - 30,000Å |
| Back Side Metalization | Au - 12,000Å |

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

93,826

PRINCIPAL DEVICE TYPES

CMUSH2-4 Series

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Hauppauge, NY 11788 USA
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R0 (20- January 2006)